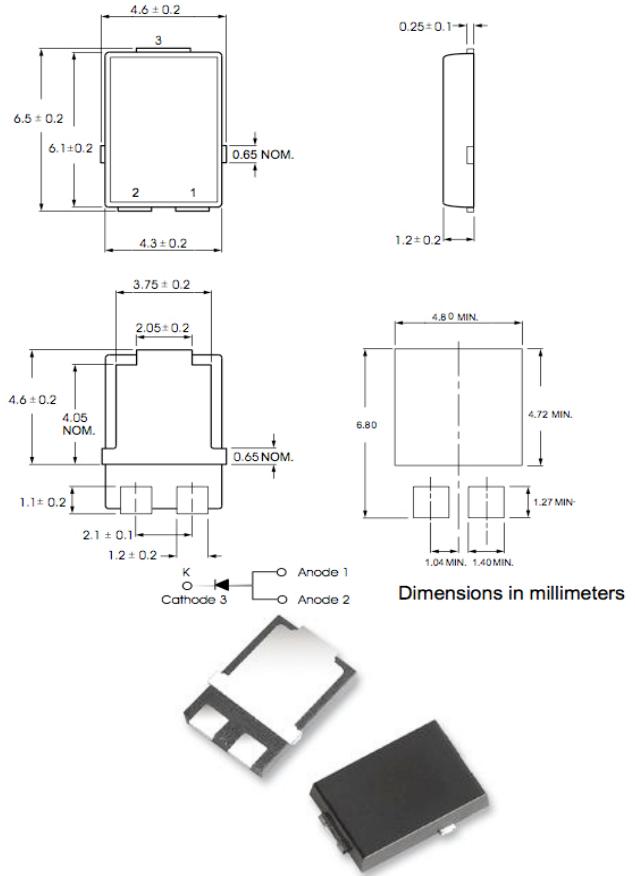


High Current Density Surface Mount Schottky Barrier Rectifiers

SSS10P30~60

FEATURES

- Very low profile - typical height of 1.1 mm
- Ideal for automated placement
- Low forward voltage drop, low power losses
- High efficiency
- Low thermal resistance
- Meets MSL level 1, per J-STD-020
- Solder dip 260 °C max. 10 s, per JESD 22-A111
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



MECHANICAL DATA

Case: Conform to JEDEC TO-277A

Molding compound meets UL 94 V-0 flammability

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	SS10P30	SS10P40	SS10P45	SS10P60	Unit
Maximum repetitive peak reverse voltage	VRRM	30	40	45	60	V
Working peak reverse voltage	VRWM	30	40	45	60	V
Maximum DC blocking voltage	VDC	30	40	45	60	V
Maximum average forward rectified current Total device	IF(AV)	10				A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	300				A
Non-repetitive avalanche energy at 25 °C IAS = 2 A per diode	EAS	20				mJ
Operating junction temperature range	TJ	-55 to +150				°C
Storage temperature range	TSTG	-55 to +150				°C

Electrical characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Value				Unit
Maximun instantaneous at IF=10A, Tj=25°C	VF	0.51	0.51	0.51	0.63	
at IF=5A, Tj=25°C		0.45	0.45	0.45	0.65	V
forward voltage per leg						
at IF=10A, Tj=125°C		0.43	0.43	0.43	0.53	
Maximum reverse current per leg Tj=25°C	IR	300				u'A
at working peak reverse voltage Tj=125°C		50				m'A

Thermal characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol			Unit
Typical thermal resistance	RθJA	60		°C/W
	Rthjc	3		

Notes:

- (1) Pulse test: 300 μs pulse width, 1 % duty cycle
- (2) Pulse test: Pulse width ≤ 40 ms